25V N-Channel Enhancement Mode MOSFET

V_{DS}=25V

$R_{DS(ON)}$, Vgs@10V,Ids@30A ≦ 9mΩ

$R_{DS(ON)}$, Vgs@ 5V,Ids@15A ≦18mΩ

FEATURES

Advanced trench process technology

High density cell design for ultra low on-resistance

Specially designed for DC/DC converters and motor drivers

Fully characterized avalanche voltage and current

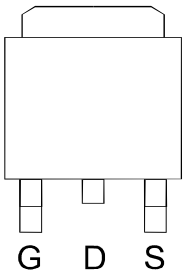
APPLICATIONS

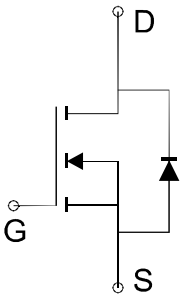
- Motherboard (V-Core)
- DC/DC Converter
- Load Switch
- LCD Display inverter
- IPC

PIN CONFIGURATION

(TO-252)

Top View





Absolute Maximum Ratings (T_A=25℃ Unless Otherwise Noted)

Parameter		Symbol	Limit		Unit
Drain-Source Voltage		V_{DSS}	25		V
Gate-Source Voltage		V_{GSS}	±20		V
Continuous Drain Current(Tj=150℃)*	T_C=25℃	I_D	53		A
Pulsed Drain Current		I_{DM}	100		A
Maximum Power Dissipation	T_C=25℃	P_D	40		W
	T_C=70℃		25		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150		℃
Avalanche Energy with Single Pulse(L=0.1mH,Rg=25Ω)		E_{AS}	50		mJ
Thermal Resistance-Junction to Ambient*		$R_{\theta JA}$	T≦10 sec	15	℃/W
			Steady State	40	
Thermal Resistance-Junction to Case		$R_{\theta JC}$	3.1		℃/W

*The device mounted on 1in^2 FR4 board with 2 oz copper

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Electrical Characteristics (T_A=25℃ Unless Otherwise Specified)

Symbol	Parameter	Limit	Min	Typ	Max	Unit
STATIC						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	25			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1		3	V
I_{GSS}	Gate-Body Leakage	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=25V, V_{GS}=0V			1	μA
$R_{DS(ON)}$	Drain-Source On-Resistance	V_{GS}=10V, I_D=30A		6.7	9	mΩ
		V_{GS}= 5V, I_D=15A		13	18	
DYNAMIC						
Qg	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_D=25A		22		nC
Qg	Total Gate Charge	V_{DS}=15V, V_{GS}=4.5V, I_D=25A		11		
Qgs	Gate-Source Charge			5.4		
Qgd	Gate-Drain Charge			5.5		
Ciss	Input Capacitance	V_{DS}=15V, V_{GS}=0V, f=1MHz		840		pF
Coss	Output Capacitance			180		
Crss	Reverse Transfer Capacitance			55		
Rg	Gate Resistance	V_{DS}=0V, V_{GS}=0V, f=1MHz		1		Ω
$t_{d(on)}$	Turn-On Delay Time	R_L=15Ω, V_{GEN} =10V, I_D=1A V_{DD}=15V, R_G=3Ω		13.5		ns
t_r	Turn-On Rise Time			13		
$t_{d(off)}$	Turn-Off Delay Time			42		
t_f	Turn-Off Fall Time			4		
SOURCE-DRAIN DIODE						
I_S	Max.Diode Forward Current				20	A
V_{SD}	Diode Forward Voltage	I_S=20A, V_{GS}=0V		0.87	1.5	V

Note: Pulse test: pulse width＜=300us, duty cycle＜=2%

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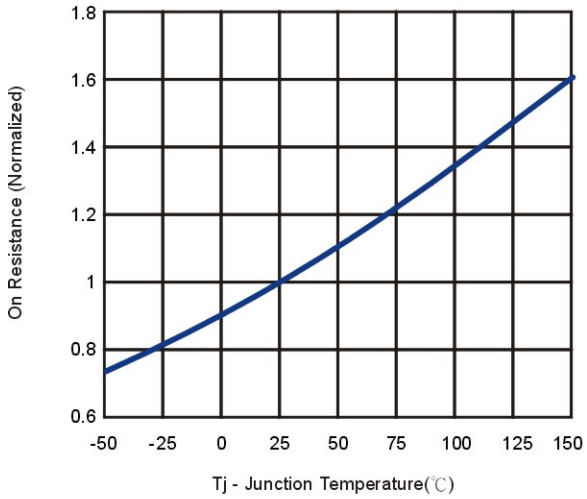
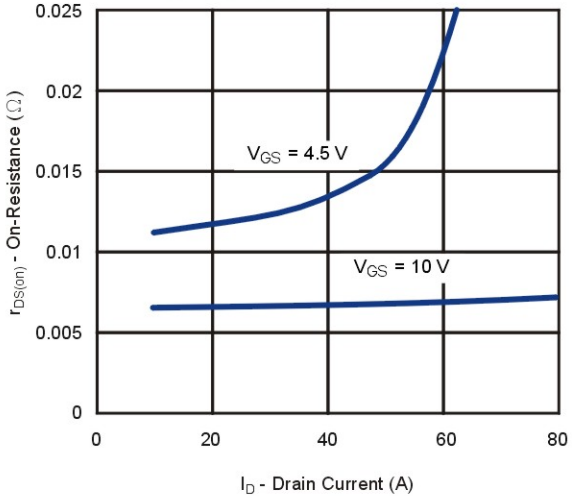
Typical Characteristics (T_J =25℃ Noted)

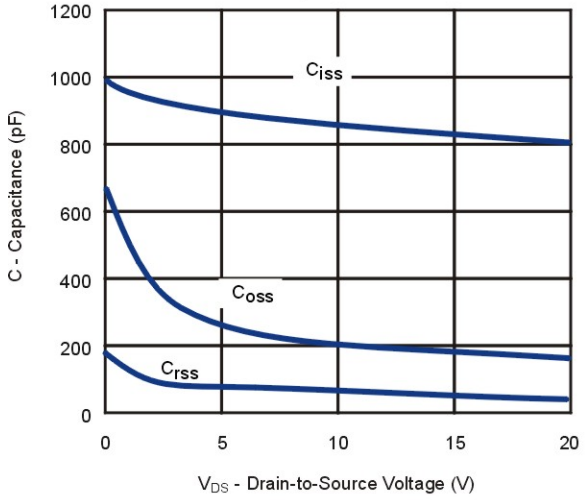
On Resistance vs. Junction Temperature



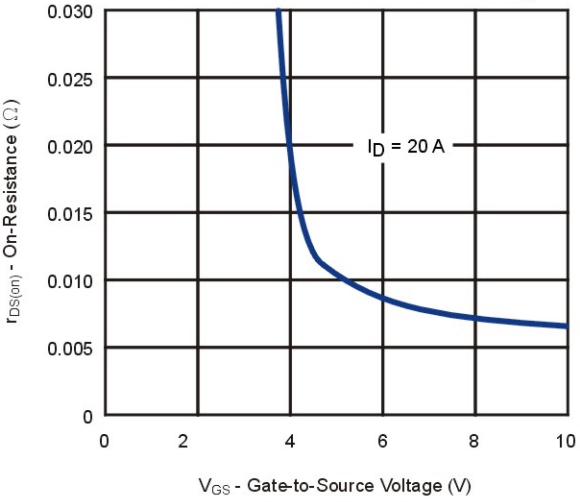
On-Resistance vs. Drain Current



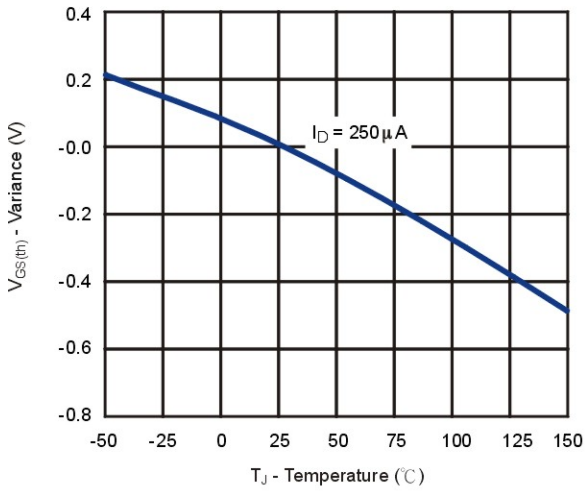
Capacitance



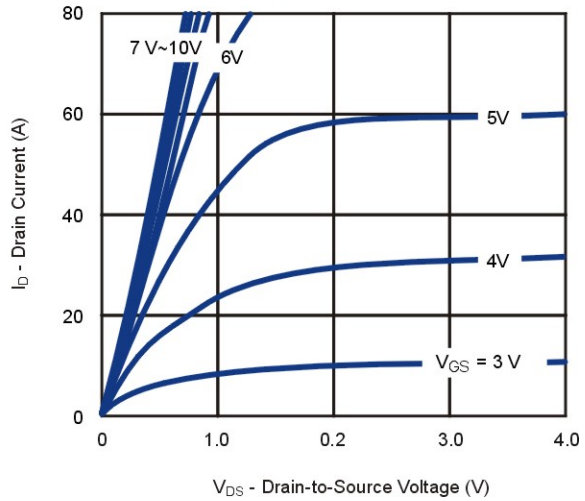
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



On-Region Characteristics



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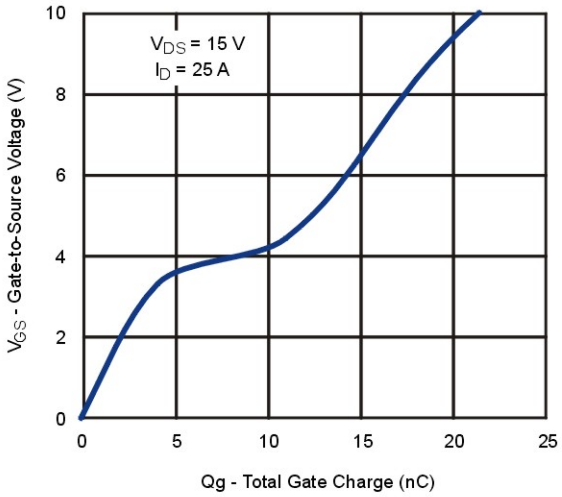
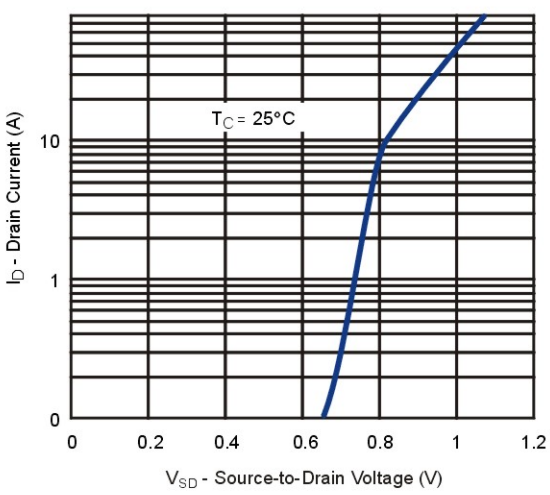
Typical Characteristics (T_J =25℃ Noted)

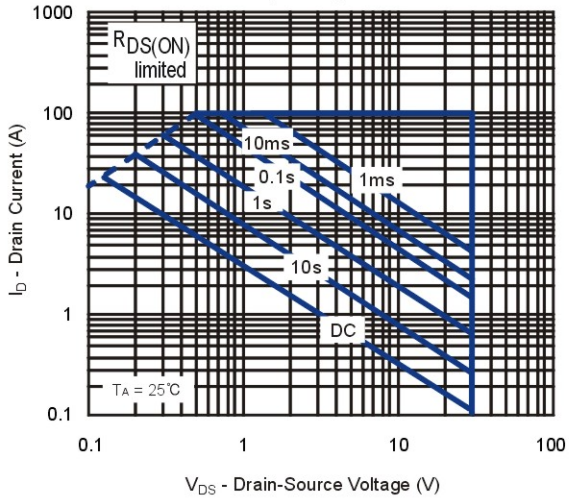
Gate Charge



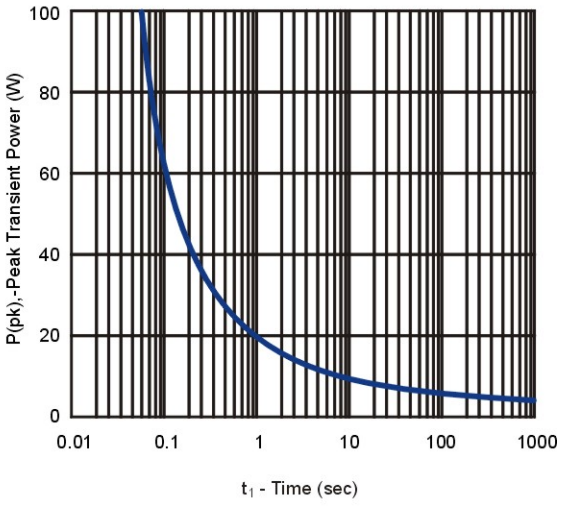
On-Resistance vs. Drain Current



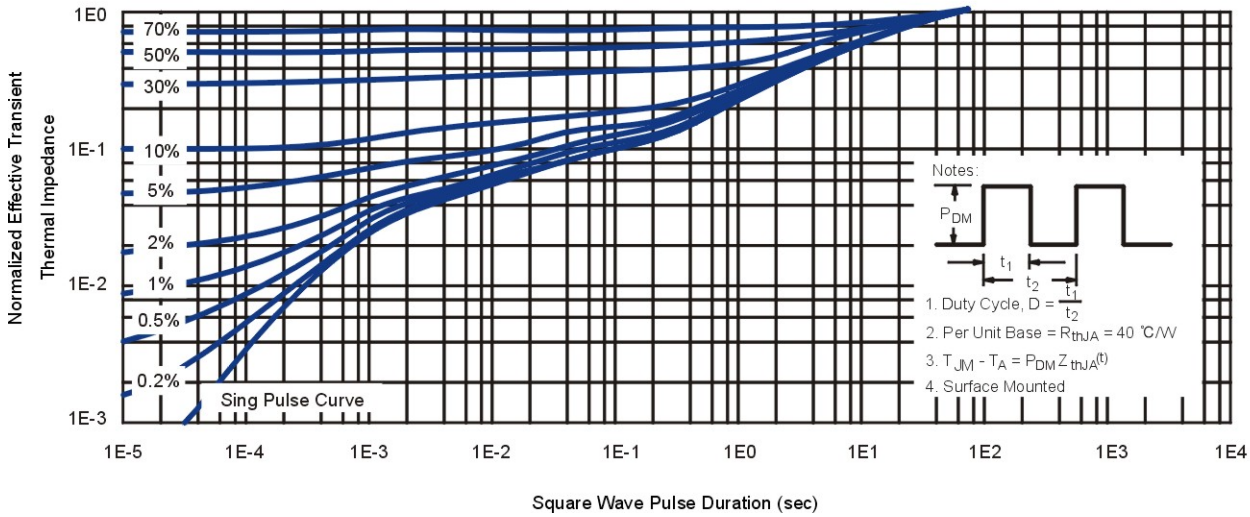
Maximum Forward Biased Safe Operating Area



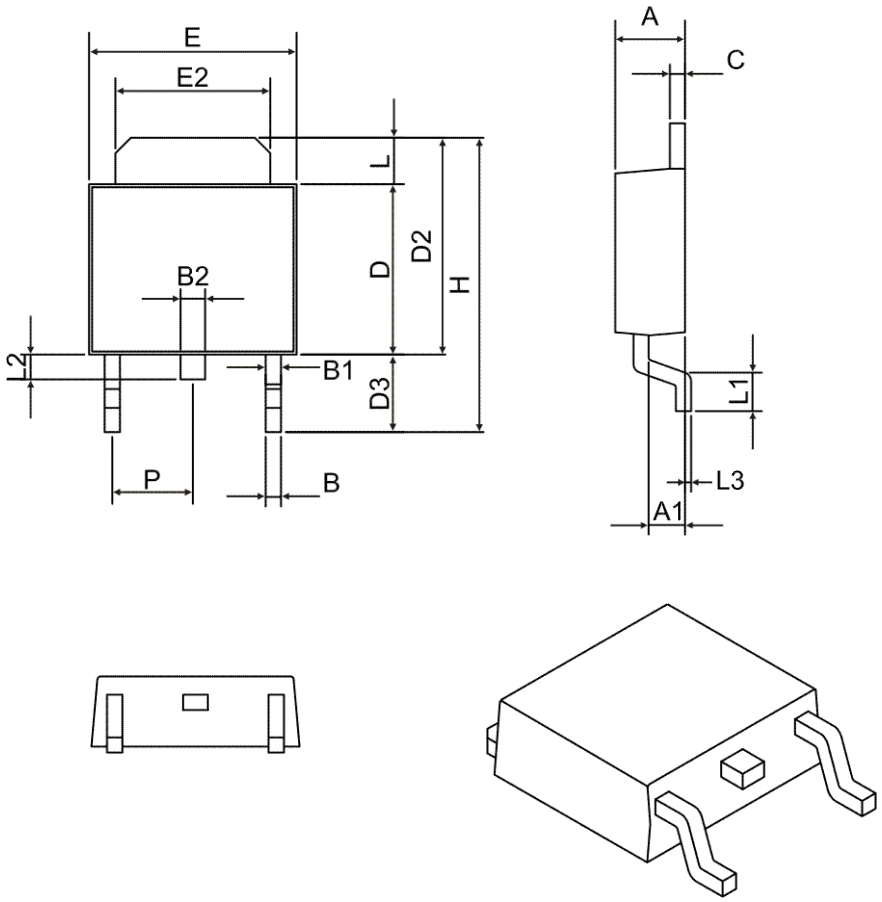
Single Pulse Maximum Power Dissipation



Normalized Thermal Transient Impedance, Junction-to-Ambient



TO-252 Package Outline



SYMBOL	MILLIMETERS (mm)	
	MIN	MAX
A	2.00	2.50
A1	0.90	1.30
B	0.50	0.85
B1	0.50	0.80
B2	0.50	1.00
C	0.40	0.60
D	5.20	5.70
D2	6.50	7.30
D3	2.20	3.00
H	9.50	10.50
E	6.30	6.80
E2	4.50	5.50
L	1.30	1.70
L1	0.90	1.70
L2	0.50	1.10
L3	0	0.30
P	2.00	2.80